

isc Silicon NPN Power Transistor

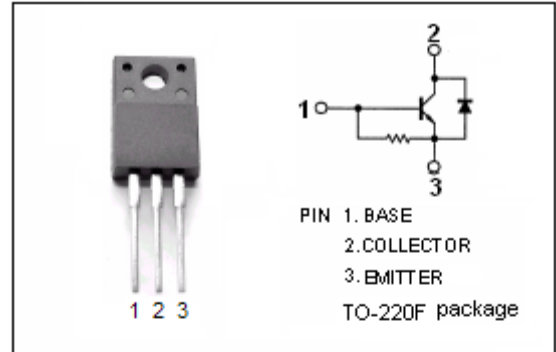
2SC5885

DESCRIPTION

- High Breakdown Voltage-
: $V_{CB0} = 1500V$ (Min)
- Wide Area of Safe Operation
- Built-in Damper Diode

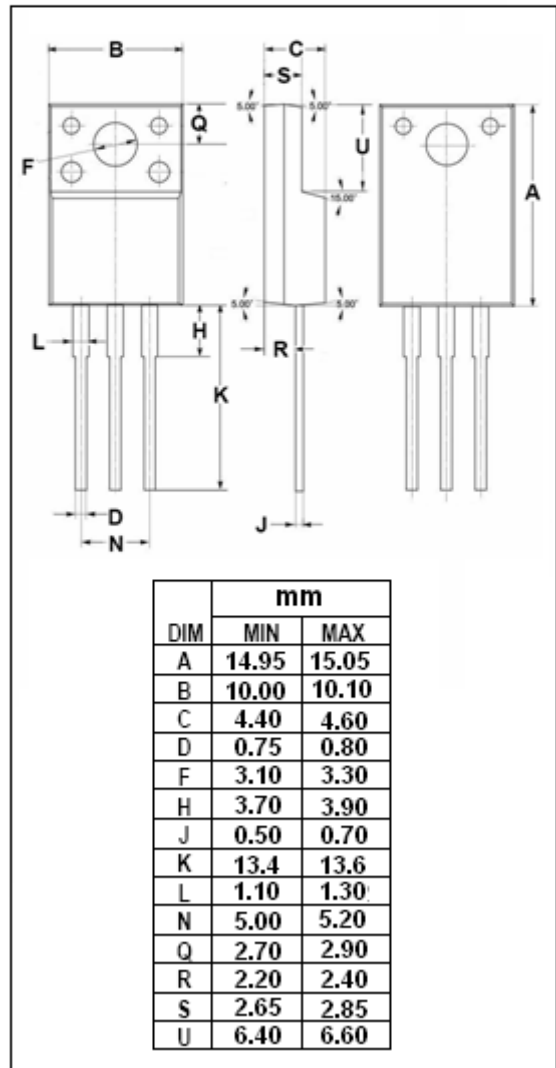
APPLICATIONS

- Horizontal deflection output for TV, CRT monitor applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CB0}	Collector-Base Voltage	1500	V
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	6	A
I_B	Base Current- Continuous	3	A
I_{CP}	Collector Current-Pulse	9	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}C$	2	W
	Collector Power Dissipation @ $T_c=25^{\circ}C$	30	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SC5885****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 500mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.75A			2.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 3A; I _B = 0.75A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 1000V; I _E = 0 V _{CB} = 1500V; I _E = 0			50 1.0	μ A mA
h _{FE}	DC Current Gain	I _C = 3A; V _{CE} = 5V	5		10	
V _{ECF}	C-E Diode Forward Voltage	I _F = 3A			2.0	V
f _T	Current-Gain—Bandwidth Product	I _C = 0.1A; V _{CE} = 10V; f= 0.5MHz		3		MHz

Switching times; Resistive load

t _{stg}	Storage Time	I _C = 3A, I _{B1} = 0.75A; I _{B2} = -1.5A			5.0	μ s
t _f	Fall Time				0.5	μ s